NSN 5962-01-351-5722

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-351-5722

Overall Height:
0.400 inches
Body Length:
1.280 inches
Body Width:
Between 0.220 inches and 0.310 inches
Body Height:
Between 0.140 inches and 0.185 inches
Maximum Power Dissipation Rating:
1.2 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
Radar set an/sps-4 (v) 7
Features Provided:
Hermetically sealed and burn in and monolithic and electrostatic sensitive and ultraviolet erasable
Inclosure Material:
Ceramic
Inclosure Configuration:
-
Dual-in-line
Dual-in-line
Dual-in-line Output Logic Form:
Dual-in-line Output Logic Form: Complementary-metal oxide-semiconductor logic
Dual-in-line Output Logic Form: Complementary-metal oxide-semiconductor logic Input Circuit Pattern:
Dual-in-line Output Logic Form: Complementary-metal oxide-semiconductor logic Input Circuit Pattern: 22 input
Dual-in-line Output Logic Form: Complementary-metal oxide-semiconductor logic Input Circuit Pattern: 22 input Case Outline Source And Designator:
Dual-in-line Output Logic Form: Complementary-metal oxide-semiconductor logic Input Circuit Pattern: 22 input Case Outline Source And Designator: D-9 mil-m-38510
Dual-in-line Output Logic Form: Complementary-metal oxide-semiconductor logic Input Circuit Pattern: 22 input Case Outline Source And Designator: D-9 mil-m-38510 Current Rating Per Characteristic:
Dual-in-line Output Logic Form: Complementary-metal oxide-semiconductor logic Input Circuit Pattern: 22 input Case Outline Source And Designator: D-9 mil-m-38510 Current Rating Per Characteristic: 100.00 milliamperes reverse current, dc absolute
Dual-in-line Output Logic Form: Complementary-metal oxide-semiconductor logic Input Circuit Pattern: 22 input Case Outline Source And Designator: D-9 mil-m-38510 Current Rating Per Characteristic: 100.00 milliamperes reverse current, dc absolute Terminal Surface Treatment:
Dual-in-line Output Logic Form: Complementary-metal oxide-semiconductor logic Input Circuit Pattern: 22 input Case Outline Source And Designator: D-9 mil-m-38510 Current Rating Per Characteristic: 100.00 milliamperes reverse current, dc absolute Terminal Surface Treatment: Solder
Dual-in-line Output Logic Form: Complementary-metal oxide-semiconductor logic Input Circuit Pattern: 22 input Case Outline Source And Designator: D-9 mil-m-38510 Current Rating Per Characteristic: 100.00 milliamperes reverse current, dc absolute Terminal Surface Treatment: Solder Product Name:
Dual-in-line Output Logic Form: Complementary-metal oxide-semiconductor logic Input Circuit Pattern: 22 input Case Outline Source And Designator: D-9 mil-m-38510 Current Rating Per Characteristic: 100.00 milliamperes reverse current, dc absolute Terminal Surface Treatment: Solder Product Name: And-or-logic array

Pal

10.00 input picofarads and 10.00 output picofarads

Time Rating Per Chacteristic: 25.00 nanoseconds delay Memory Device Type:

NSN 5962-01-351-5722

Memory Microcircuit - Page 2 of 2



Test	Data	Docu	ıment
------	------	------	-------

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

24 printed circuit

Shelf Life:

N/a

Unit Of Measure:

--

Demilitarization:

Yes - demil/mli

Fiig:

A458a0